

R8A66162SP 32-BIT LED DRIVER WITH SHIFT REGISTER AND LATCH

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DESCRIPTION

The R8A66162SP is a semiconductor integrated circuit for LED array driver with 32-bit serial-input, parallel - output shift register, equipped with direct set input and output latches.

The R8A66162SP guarantees sufficient 24mA (Vcc=5.0V case) output current to drive anode common LED, allowing 32-bit simultaneous and continuous current output. The parallel outputs are open-drain outputs. In addition, as this product has been designed in complete CMOS, power consumption can be greatly reduced when compared with conventional BIPOLAR or Bi-CMOS products. Furthermore, pin layout ensures the realization of an easy printed circuit. R8A66162SP is the succession product of M66313FP.

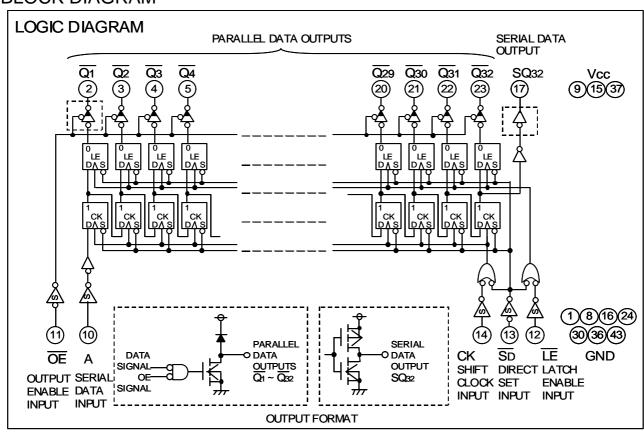
FEATURES

- Anode common LED drive
- Vcc 5V or 3.3V single power supply
- High output current: All parallel outputs $\overline{Q_1} \sim \overline{Q_{32}}$ IOL=24mA (at Vcc=5.0V), IOL=12mA (at Vcc=3.3V), LEDs can be turned on simultaneously.
- Low power dissipation: 200uW/package (max) (VCC=5.0V, Ta=25°C, quiescent state)
- High noise margin: Employment of Schmitt-trigger circuit on all inputs allows application with long wiring.
- Direct set input (SD)
- Open-drain output $(\overline{Q_1} \sim \overline{Q_{32}})$
- Serial data output for cascading (SQ₃₂)
- Wide operating temperature range (Ta=-40°C~+85°C)
- Pin configuration for easy layout on PCB. (Pin configuration allows easy cascade connection or LED connection)

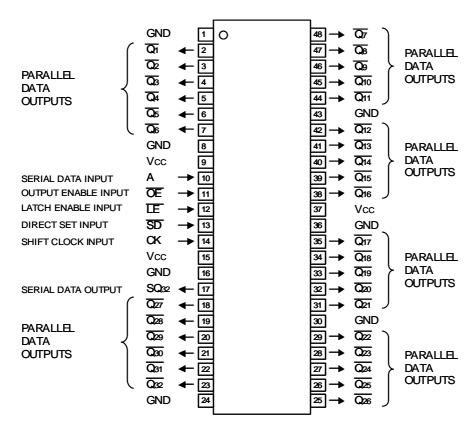
APPLICATION

- LED array drive, The various LED display modules
- PPC, Printer, VCR, Mini-compo, Button-Telephone etc. All of LED display equipments

BLOCK DIAGRAM



PIN CONFIGURATION (TOP VIEW)



FUNCTIONAL DESCRIPTION

The employment of silicon gate CMOS process of the R8A66162SP guarantees low power dissipation and maintains high noise margin as well as high output current and high speed required to drive LEDs. Each shift register bit consists of a flip-flop for shifting and an output latch.

The shift operation takes place when the shift clock input CK changes from low-level to high-level.

The serial data input A corresponds to the data input of the first-stage shift register, and the shift register is shifted in sequence when a pulse is applied to CK.

If the latch-enable input $\overline{\text{LE}}$ is turned high-level, the content of the shift register at that instant is latched. The parallel data outputs $\overline{Q_1} \sim \overline{Q_{32}}$ are open-drain outputs.

To expand the number of bits, use the serial data output SQ32 which shows the output of the shift register of the 32nd bit.

If the direct set input \overline{SD} is turned low-level, $\overline{Q_1} \sim \overline{Q_{32}}$ and SQ_{32} are set. Then shift register and latches are set. If the high-level input is applied to the output enable input \overline{OE} , $\overline{Q_1} \sim \overline{Q_{32}}$ are set to the high-impedance state, but SQ32 is not set to the high-impedance state. The shift operation is not affected when \overline{OE} is changed.

FUNCTION TABLE (Note: 1)

								_ `				<u> </u>																										
OPERATION		IN	IPU	Т																PAF	RALI	.EL	OU ⁻	IPU	TS													SERIAL OUTPUT
MODE	 SD	ск	<u>_</u>	Α	Œ	<u>_</u>	_ Q₂	Q ₃	Q ₄	Q ₅	Q ₅	Q ₇	Q ®	Q _a	Q10	Q ₁₁	— Q12	— Q13	Q ₁₄	Q ₁₅	Q ₁₆	Q17	— Q18	Q19	— Q20	Q ₂₁	Q22	— Q23	Q ₂₄	— Q25	Q ₂₆	Q ₂₇	Q28	Q29	Q30	Q31	— Q32	SQ₃₂ SQ₃₂
SET	L	х	х	х	L	L	L	L	L	L	Г	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	L	н
0	Н		L	Н	L	L	Q٩	Q ⁰ 2	Q ⁰ 3	Q⁰₄	Q ⁰ ₅	Q%	Q [®] 7	Q⁰s	Q%	Qº10	Q ⁰ 11	Q ⁰ 12	Q ⁰ 13	Q ⁰ 14	Q ⁰ 15	Q ⁰ 16	Q ⁰ 17	Q ⁰ 18	Q ⁰ 19	Q ⁰ 20	Q ⁰ 21	Q ⁰ 22	Q ⁰ 23	Q ⁰ 24	Q ⁰ 25	Q ⁰ 26	Q ⁰ 27	Q ⁰ 28	Q ⁰ 29	Q ⁰ 30	Q ⁰ 31	q ⁰ 31
SHIFT	н		L	L	L	z	Qº1	Q ⁰ ₂	Q ⁰ 3	Q°₄	 Q⁰₅	Qº6	Q ⁰ 7	Qºs	Qº9	Q ⁰ 10	Q ⁰ 11	Q ⁰ 12	Q ⁰ 13	Q ⁰ 14	Q ⁰ 15	Q ⁰ 16	Q ⁰ 17	Q ⁰ 18	Q ⁰ 19	Q ⁰ 20	Q ⁰ 21	Q ⁰ 22	Q ⁰ 23	Q ⁰ 24	 Q ⁰ 25	 Q ⁰ 26	Q ⁰ 27	Q ⁰ 28	Q ⁰ 29	Q ⁰ 30	Q ⁰ 31	q ⁰ 31
LATCH	н	х	Н	х	L	Q°1	Q ⁰ ₂	Q ⁰ ₃	Q⁰₄	Q ⁰ 5	Q ⁰ 6	Q ⁰ 7	Q%	Q°9	Q ⁰ 10	Q ⁰ 11	Q ⁰ 12	Q ⁰ 13	Q ⁰ 14	Q ⁰ 15	Q ⁰ 16	Q ⁰ 17	Q ⁰ 18	Q ⁰ 19	Q ⁰ 20	Q ⁰ 21	Q ⁰ 22	Q ⁰ 23	Q ⁰ 24	Q ⁰ 25	Q ⁰ 26	Q ⁰ 27	Q ⁰ 28	Q ⁰ 29	Q ⁰ 30	Q ⁰ 31	Q ⁰ 32	q 32
OUTPUT DIS- ABLE		х	х	х	н	z	z	z	z	z	z	z	z	z	z	z	z	z	z	z	z	z	z	z	z	z	z	z	z	z	z	z	z	z	z	z	z	q 32

Note 1. : Transition from low-to-high-level : Shows the status of output \overline{Q} before CK input changes X : Irrelevant

 $q^0\,:\, \underline{\text{The content of shift register before CK changes}}$

q : The content of shift registerZ : High-impedance state

ABSOLUTE MAXIMUM RATINGS (Ta=-40~85°C, unless otherwise noted)

Symbol	Parameter		Conditions	Ratings	Unit
Vcc	Supply voltage			-0.5~+7.0	V
V_{I}	Input voltage			-0.5~Vcc+0.5	V
Vo	Output voltage			-0.5~Vcc+0.5	V
lo	Output current per output pin	$\overline{Q}_1 \sim \overline{Q}_{32}$		50	mA
		SQ ₃₂		±25	
Icc	Supply/GND current		Vcc, GND	-920, +20	mA
P_d	Power dissipation			650	mW
T_{stq}	Storage temperature range			-65~150	°C

RECOMMENDED OPERATING CONDITIONS (Ta=-40~85°C, unless otherwise noted)

Symbol	Parameter				Unit	
			Min.	Тур.	Max.	
Vcc	Supply voltage	5.0V support	4.5	5.0	5.5	V
		3.0	3.3	3.6	V	
V_{I}	Input voltage		0		Vcc	V
Vo	Output voltage	0		Vcc	V	
T _{opr}	Operating temperature range	-40		85	°C	

ELECTRICAL CHARACTERISTICS

■5.0V version support specifications (Ta=-40~85°C, Vcc=4.5V~5.5V, unless otherwise noted)

Symbol	Paramet	er	Test co	nditions		Limits		Unit
					Min.	Тур.	Max.	
V_{T+}	Positive going threshold voltage	1			0.35xVcc		0.70xVcc	V
V _T -	Negative going threshold voltage				0.20xVcc		0.55xVcc	V
V _{OH}	High level	SQ ₃₂	$V_I = V_{T+}, V_{T-}$	I _{OH} =-20uA	Vcc-0.1			V
	output voltage		Vcc=4.5V	I _{OH} =-4mA	3.66			
V_{OL}	Low level	$\overline{Q}_1 \sim \overline{Q}_{32}$	$V_I=V_{T+},\ V_{T-}$	I _{OL} =20uA			0.10	V
	output voltage		Vcc=4.5V	I _{OL} =24mA			0.50	
				I _{OL} =28mA			0.55 _(Note2)	
		SQ ₃₂		I _{OL} =20uA			0.10	
				I _{OL} =4mA			0.53	
I _{IH}	High level input of	urrent	V _I =Vcc	Vcc=5.5V			5	uA
I _{IL}	Low level input c	urrent	V _I =GND	Vcc=5.5V			-5	uA
Ιο	Maximum	$\overline{Q}_1 \sim \overline{Q}_{32}$	$V_I=V_{T+}, V_{T-}$	V _O =Vcc			10	uA
	output		Vcc=5.5V	V _O =GND			-10	
	leakage current			-				
Icc	Quiescent supply	current	V _I =Vcc, GND	Vcc=5.5V			400	uA

Note2 : Ta = -40~70°C

■3.3V version support specifications (Ta=-40~85°C, Vcc=3.0V~3.6V, unless otherwise noted)

Symbol	Paramete	er	Test co	nditions		Limits		Unit
					Min.	Тур.	Max.	
V_{T+}	Positive going threshold voltage				0.35xVcc		0.70xVcc	V
V _{T-}	Negative going threshold voltage				0.20xVcc		0.55xVcc	V
V _{OH}	High level	SQ ₃₂	$V_I = V_{T+}, V_{T-}$	I _{OH} =-20uA	Vcc-0.1			V
	output voltage		Vcc=3.0V	I _{OH} =-2mA	2.60			
V_{OL}	Low level	$\overline{Q}_1 \sim \overline{Q}_{32}$	$V_I = V_{T+}, V_{T-}$	I _{OL} =20uA			0.10	V
	output voltage		Vcc=3.0V	I _{OL} =12mA			0.54	
		SQ ₃₂		I _{OL} =20uA			0.10	
				I _{OL} =2mA			0.40	
I _{IH}	High level input of	urrent	V _I =Vcc	Vcc=3.6V			5	uA
I _{IL}	Low level input co	urrent	V _I =GND	Vcc=3.6V			-5	uA
lo	Maximum	$\overline{Q}_{1} \sim \overline{Q}_{32}$	$V_I = V_{T+}, V_{T-}$	V _O =Vcc			10	uA
	output leakage current		Vcc=3.6V	V _O =GND			-10	
Icc	Quiescent supply	current	V _I =Vcc, GND	Vcc=3.6V			400	uA

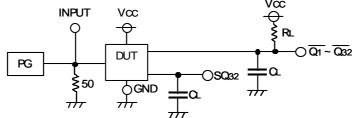
SWITCHING CHARACTERISTICS (Ta=-40~85 °C, Vcc=5.0V or 3.3V, unless otherwise noted)

Symbol	Paramete	r	Test	5.0V	specifi	cation	3.3V s	Unit		
			conditions	Min.	Тур.	Max.	Min.	Тур.	Max.	
f _{max}	Maximum clock frequent	су				4			3.3	MHz
tPZL	Output "Z-L" and "L-Z"	CK-Q ₁ ~Q ₃₂				200			220	ns
	propagation time	(Turned on)								
tPLZ		$CK-\overline{Q}_1\sim\overline{Q}_{32}$				250			270	ns
		(Turned off)								
tPLH	Output "L-H" and "H-L"	CK-SQ ₃₂				125			150	ns
tPHL	propagation time					125			150	ns
tPZL	Output "Z-L"	$\overline{S}_D - \overline{Q}_1 \sim \overline{Q}_{32}$	C _L =50pF			200			220	ns
	propagation time	(Turned on)	D 410							
tPLH	Output "L-H"	\overline{S}_D -SQ ₃₂	$R_L=1k\Omega$			125			150	ns
	propagation time		(NI=4=2)							
tPZL	Output "Z-L" and "L-Z"	$\overline{\text{LE}}$ - \overline{Q}_1 ~ \overline{Q}_{32}	(Note3)			125			150	ns
	propagation time	(Turned on)								
tPLZ		\overline{LE} - $\overline{Q}_1 \sim \overline{Q}_{32}$				200			220	ns
		(Turned off)								
tPZL	Output "Z-L" and "L-Z"	\overline{OE} - $\overline{Q}_1 \sim \overline{Q}_{32}$				125			150	ns
	propagation time	(Turned on)								
tPLZ		\overline{OE} - $\overline{Q}_1 \sim \overline{Q}_{32}$				200			220	ns
		(Turned off)								
Cı	Input capacitance					10			10	pF
Co	Output capacitance		OE=Vcc			15			15	pF

TIMING REQUIREMENTS (Ta=-40~85 $^{\circ}$ C, Vcc=5.0V or 3.3V, unless otherwise noted)

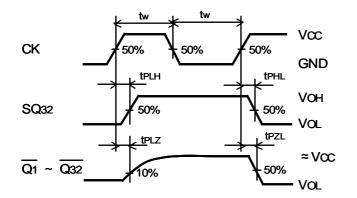
Symbol	Parameter	Test	5.0V	specific	cation	3.3\	specific	cation	Unit
		conditions	Min.	Тур.	Max.	Min.	Тур.	Max.	
t _w	CK, LE, S _D pulse width		125			150			ns
t _{su}	Setup time A to CK		125			150			ns
t _h	Hold time A to CK	(Note3)	15			20			ns
	Hold time LE to CK		70			80			ns
t _{rec}	Recovery time CK to S _D		70			80			ns

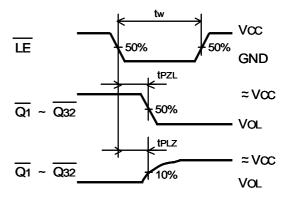


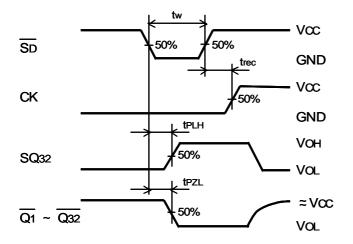


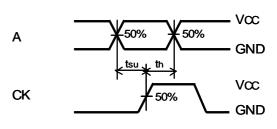
- (1) The pulse generator(PG) has the following characteristics(10%~90%):tr=6ns,tf=6ns
- (2) The capacitance CL includes stray wiring capacitance and the probe input capacitance.

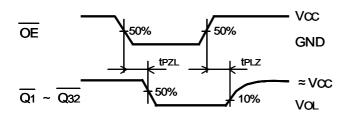
TIMING DIAGRAM

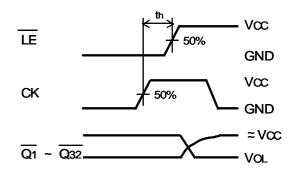






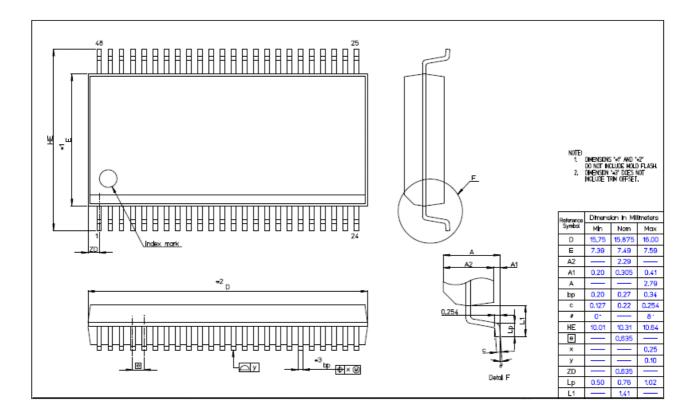






PACKAGE OUTLINE

Package	RENESAS Code	Previous Code
48pin SSOP	PRSP0048ZB-A	48P2X-A



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